









CEB85N75V

75V Δ 10mΩ Δ 85A Δ Si MOSFET

SILICON Si MOSFET ▲ SMD type

N-channel enhancement mode

UL94V-0 rated flame retardant epoxy

TO263 (D2PAK) package ▲ MSL 3

Super high dense cell density for extremely low R_{DS(ON)}

High power and current handling capability

MAXIMUM RATINGS

Parameter (T _C = 25°C, unless otherwise noted)	Characteristics	
Drain-Source Voltage	V _{DS}	75V
Gate-Source Voltage	V _{GS}	±30V
Continuous Drain Current at T _C = 25°C	I D	85A
Continuous Drain Current at T _C = 100°C	I D	59A
Pulsed Drain Current Note 1	I _{DM} Note 5	340A
Maximum Power Dissipation at T _C = 25°C	P _D	200W
Power Dissipation Derating above 25°C	ΔP_D	1.33W/°C
Single Pulsed Avalanche Energy Note 4	E _{AS}	880mJ
Single Pulsed Avalanche Current Note 4	I _{AS}	45A
Operating and Storage Temperature Range	T _J , T _{STG}	-55°C to +175°C

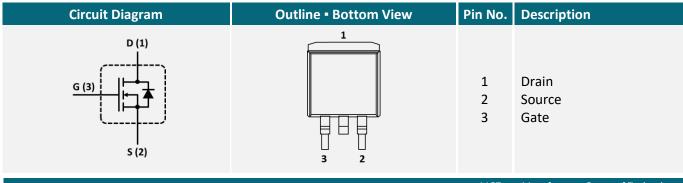
THERMAL CHARACTERISTICS

Parameter	Symbol	Limit
Thermal Resistance, Junction-to-Case	R _{TH_JC}	0.75°C/W
Thermal Resistance, Junction-to-Ambient	R _{TH JA}	62.5°C/W

APPLICATIONS

Audio	Battery Management	Industrial	Power	UPS
Amplifier	Systems	Control	Inverter	
(((+4-			

PIN DESCRIPTION



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ELECTRICAL CHARACTERISTICS ▲ T_C = 25°C, unless otherwise noted

Item	Condition	Condition Symbol			Max.	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250\mu A$	BV_{DSS}	75			V
Zero Gate Voltage Drain Current	$V_{DS} = 75V$, $V_{GS} = 0V$	I _{DSS}			1	μΑ
Gate Body Leakage Current, Forward	$V_{GS} = 30V, V_{DS} = 0V$	I_{GSSF}			100	nA
Gate Body Leakage Current, Reverse	$V_{GS} = -30V, V_{DS} = 0V$	I_{GSSR}			-100	nA
On Characteristics Note 2						
Gate Threshold Voltage	$V_{GS} = V_{DS}$, $I_{D} = 250 \mu A$	$V_{GS(th)}$	3		5	V
Static Drain-Source On-Resistance	$V_{GS} = 12V$, $I_D = 40A$	R _{DS(ON)}		10	12	mΩ
Static Drain-Source On-Resistance	$V_{GS} = 10V$, $I_D = 40A$	R _{DS(ON)}		10.5	13	mΩ
Dynamic Characteristics Note 3						
Input Capacitance	$V_{DS} = 25V$, $V_{GS} = 0V$, $f = 1MHz$	C _{ISS}		3450		pF
Output Capacitance	$V_{DS} = 25V$, $V_{GS} = 0V$, $f = 1MHz$	Coss		670		pF
Reverse Transfer Capacitance	$V_{DS} = 25V$, $V_{GS} = 0V$, $f = 1MHz$		3		pF	
Switching Characteristics Note 3						
Turn-On Delay Time	$V_{DD} = 37.5V$, $V_{GS} = 10V$, $I_D = 45A$, $R_{G(ext)} = 4.7\Omega$	t _{D(ON)}		32		ns
Turn-On Rise Time	V_{DD} = 37.5V, V_{GS} = 10V, I_{D} = 45A, $R_{G(ext)}$ = 4.7 Ω	t_{R}		7		ns
Turn-Off Delay Time	$V_{DD} = 37.5V$, $V_{GS} = 10V$, $I_D = 45A$, $R_{G(ext)} = 4.7\Omega$	t _{D(OFF)}		54		ns
Turn-Off Fall Time	$V_{DD} = 37.5V$, $V_{GS} = 10V$, $I_D = 45A$, $R_{G(ext)} = 4.7\Omega$	t _F		13		ns
Total Gate Charge	$V_{DS} = 60V$, $V_{GS} = 10V$, $I_D = 75A$	Q_{G}		64		nC
Gate Source Charge	$V_{DS} = 60V$, $V_{GS} = 10V$, $I_D = 75A$	Q_{GS}		18		nC
Gate Drain Charge	$V_{DS} = 60V$, $V_{GS} = 10V$, $I_D = 75A$	Q_{GD}		13		nC
Drain-Source Diode Characteristics ar	nd Maximum Ratings					
Drain-Source Diode Forward Current		Is			85	Α
Drain-Source Diode Forward Voltage Note 2	$V_{GS} = 0V$, $I_S = 40A$	V_{SD}			1.5	V

Notes

- 1: Repetitive Rating: Pulse width limited by maximum junction temperature.
- 2: Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2%.
- 3: Guaranteed by design, not subject to production testing.
- 4: L = 0.87mH, I_{AS} = 45A, V_{DD} = 38V, R_{G} = 25Ω, Starting T_{J} = 25°C.
- 5: Pulse width limited by safe operating area.

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REFERENCE DATA A TYPICAL DEVICE PERFORMANCE

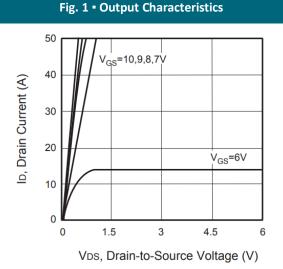


Fig. 2 • Transfer Characteristics

120
100
75
50
25°C
1,=125°C
1,=125°C
1,=55°C

Ib, Drain Current (A)

0

0

Vgs, Gate-to-Source Voltage (V)

6000 5000 4000 2000 C_{iss} C_{oss} C_{rss}

Fig. 3 • Capacitance

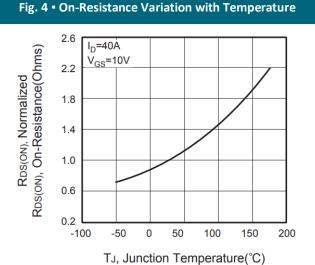


Fig. 5 • Gate Threshold Variation with Temperature

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VDS, Drain-to-Source Voltage (V)

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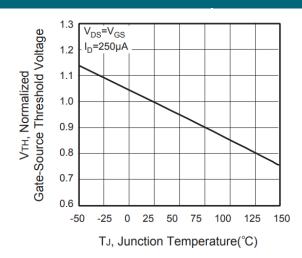
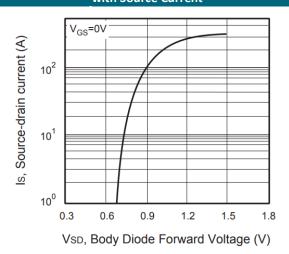


Fig. 6 • Body Diode Forward Voltage Variation with Source Current



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REFERENCE DATA A TYPICAL DEVICE PERFORMANCE

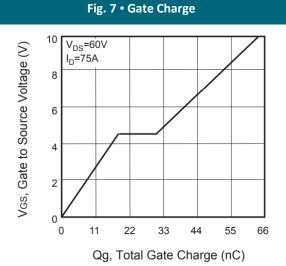


Fig. 8 • Maximum Safe Operating Area

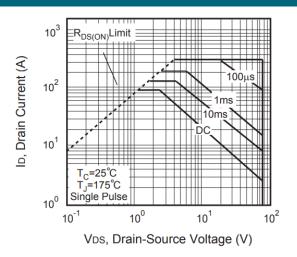
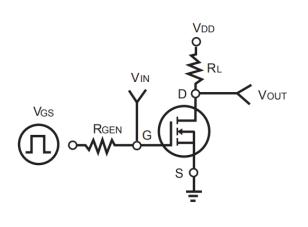


Fig. 9 • Switching Test Circuit

Fig. 10 • Switching Waveforms



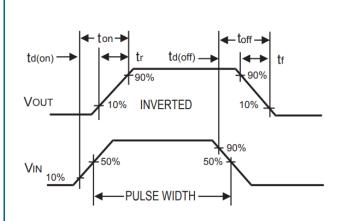
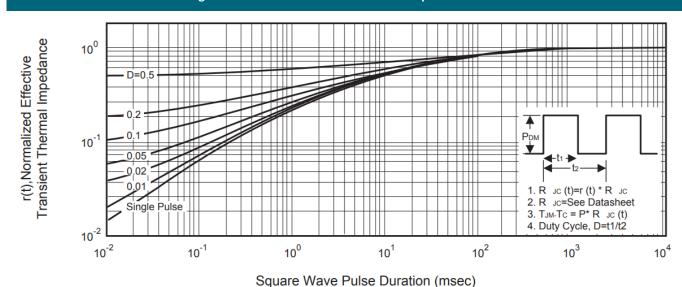


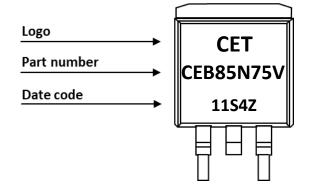
Fig. 12 - Normalized Thermal Transient Impedance Curve



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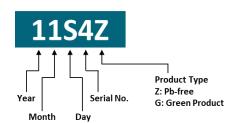


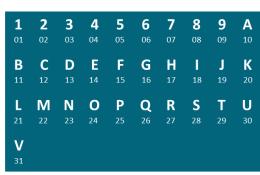
PART MARKING



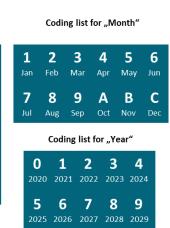
DATE CODE

Example: 11S4Z



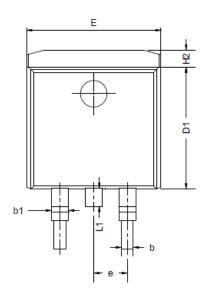


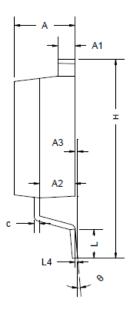
Coding list for "Day"

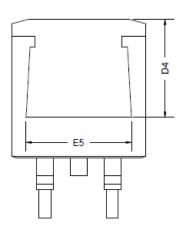


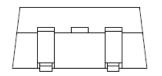


PACKAGE OUTLINE









Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)	
Α	4.37	4.57	4.77	
A1	1.22	1.27	1.42	
A2	2.49	2.69	2.89	
A3	0.00	0.13	0.25	
b	0.70	0.81	0.96	
b1	1.17	1.27	1.47	
С	0.30	0.38	0.53	
D1	8.50	8.70	8.90	
D4	6.60	-	-	

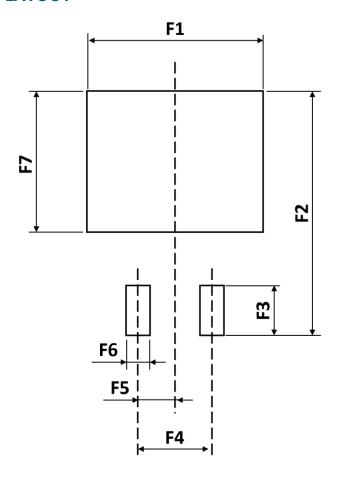
Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)				
Е	9.86	10.16	10.36				
E5	7.06	-	-				
e	2.54 BSC						
Н	14.70	14.70 15.10					
H2	1.07	1.27	1.47				
L	2.00	2.30	2.60				
L1	1.40	1.55	1.70				
L4	0.25 BSC						
θ	0°	5°	9°				

ORDERING INFORMATION

Part Number	Package	Packing	Reel Qty.	Inner Box Qty.	Outer Box Qty.
CEB85N75V	TO263 (D2PAK)	Reel	800pcs	800pcs	6,400pcs



RECOMMENDED PAD LAYOUT



Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)	
F1	-	12.20	-	
F2	- 16.90		-	
F3	-	2.54	-	
F4	-	5.08	-	

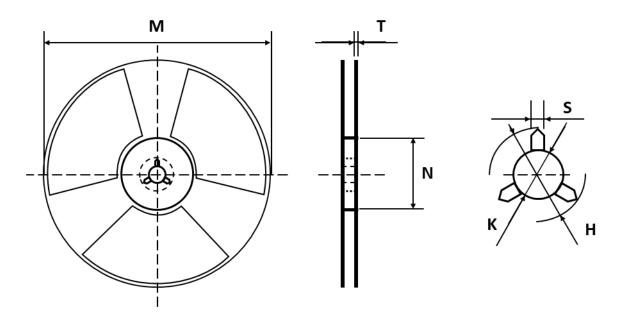
Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)
F5	-	2.54	-
F6	-	1.60	-
F7	-	9.75	-

Notes:

- 1. The suggested land pattern dimensions have been provided for reference only.
- 2. For further information, please reference document IPC-7351A.

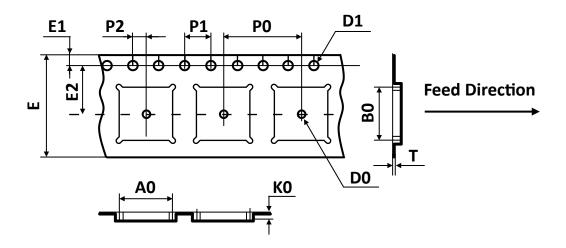


REEL DIMENSIONS ▲ All dimensions in mm



Tape Size	Reel Size	M	N	T	Н	K	S
	Ø330	Ø330.00	Ø100.00	2.10	22.00	13.00	2.00
24mm		±2.00	±0.50	±0.20	±0.50	+0.50	+0.50
		12.00	±0.50	±0.20	±0.50	-0.20	-0.20

TAPE DIMENSIONS ▲ All dimensions in mm

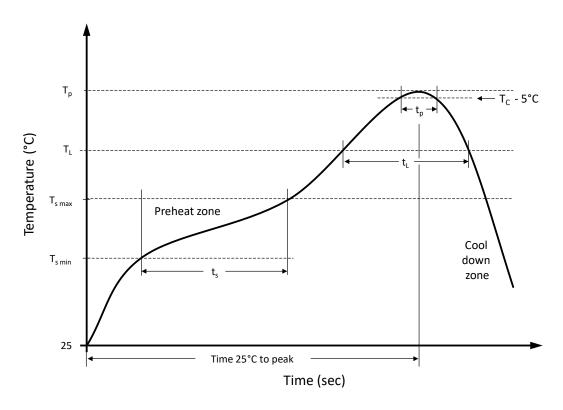


Pac	ckage	Α0	В0	КО	D0	D1	E	E1	E2	Р0	P1	P2	Т
TC	0263	10.80	16.30	4.85	1.50	1.55	24.00	1.75	11.50	16.00	4.00	2.00	0.35
(D ²	² PAK)	±0.10	±0.10	±0.10	±0.10	±0.05	±0.30	±0.10	±0.10	±0.10	±0.10	±0.10	±0.05

Note: All dimensions meet EIA-481-D requirements.



RECOMMENDED REFLOW SOLDERING PROFILE



Recommended reflow soldering conditions ▲ **Refer to JEDEC J-STD-020E**

Profile Features		Sn-Pb Eutetic Assembly	Pb-Free Assembly
Preheat temperature min.	$T_{s min}$	100 °C	150 °C
Preheat temperature max.	T _{s max}	150 °C	200 °C
Preheat time t _s from T _{s min} to T _{s max}	ts	120 seconds	120 seconds
Ramp-up rate (T₁ to Tp)		max. 3 °C/second	max. 3 °C/second
Liquidous temperature	T_L	183 °C	217 °C
Time t _L maintained above T _L	t _L	150 seconds max.	150 seconds max.
Peak package body temperature	Tp	235°C	260°C
Timeframe of within 5°C below and up to max actual peak body temperature	t _p	20 seconds max.	30 seconds max.
Ramp-down rate (T _L to T _p)		max. 6 °C/second	max. 6 °C/second
Time 25°C to peak temperature		max. 6 minutes	max. 8 minutes



REVISION TABLE

Revision	Date	Status	Notes
001	30/09/2022	Initial release	Initial publication

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